

## 20MHz, High Slew Rate, Uncompensated, High Input Impedance, Operational Amplifiers

HA-2520/2525 comprise a series of operational amplifiers delivering an unsurpassed combination of specifications for slew rate, bandwidth and settling time. These dielectrically isolated amplifiers are controlled at close loop gains greater than 3 without external compensation. In addition, these high performance components also provide low offset current and high input impedance.

120V/ $\mu$ s slew rate and 200ns (0.2%) settling time of these amplifiers make them ideal components for pulse amplification and data acquisition designs. These devices are valuable components for RF and video circuitry requiring up to 20MHz gain bandwidth and 2MHz power bandwidth. For accurate signal conditioning designs the HA-2520/2525's superior dynamic specifications are complemented by 10nA offset current, 100M $\Omega$  input impedance and offset trim capability.

### Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE	PKG. DWG. #
HA7-2520-2	-55 to 125	8 Ld CERDIP	F8.3A
HA3-2525-5	0 to 75	8 Ld PDIP	E8.3
HA3-2525-5Z (See Note)	0 to 75	8 Ld PDIP (Pb-free)	E8.3
HA7-2525-5	0 to 75	8 Ld CERDIP	F8.3A

NOTE: Intersil Pb-free plus anneal products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

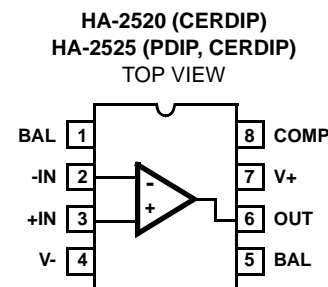
### Features

- High Slew Rate . . . . . 120V/ $\mu$ s
- Fast Settling . . . . . 200ns
- Full Power Bandwidth . . . . . 2MHz
- Gain Bandwidth ( $A_V \geq 3$ ) . . . . . 20MHz
- High Input Impedance . . . . . 100M $\Omega$
- Low Offset Current . . . . . 10nA
- Compensation Pin for Unity Gain Capability
- Pb-Free Plus Anneal Available (RoHS Compliant)

### Applications

- Data Acquisition Systems
- RF Amplifiers
- Video Amplifiers
- Signal Generators

### Pinout



# HA-2520, HA-2525

## Absolute Maximum Ratings

Supply Voltage (Between V+ and V- Terminals) . . . . .	40V
Differential Input Voltage . . . . .	15V
Output Current . . . . .	50mA

## Operating Conditions

Temperature Range	
HA-2520-2 . . . . .	-55°C to 125°C
HA-2525-5 . . . . .	0°C to 75°C

## Thermal Information

Thermal Resistance (Typical, Note 1)	$\theta_{JA}$ (°C/W)	$\theta_{JC}$ (°C/W)
PDIP Package . . . . .	96	N/A
CERDIP Package . . . . .	135	50
Maximum Junction Temperature (Hermetic Packages) . . . . .	175°C	
Maximum Junction Temperature (Plastic Package) . . . . .	150°C	
Maximum Storage Temperature Range . . . . .	-65°C to 150°C	
Maximum Lead Temperature (Soldering 10s) . . . . .	300°C	

**CAUTION:** Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

### NOTE:

- $\theta_{JA}$  is measured with the component mounted on an evaluation PC board in free air.

## Electrical Specifications $V_{SUPPLY} = \pm 15V$

PARAMETER	TEMP (°C)	HA-2520-2			HA-2525-5			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
<b>INPUT CHARACTERISTICS</b>								
Offset Voltage	25	-	4	8	-	5	10	mV
	Full	-	-	11	-	-	14	mV
Offset Voltage Drift	Full	-	20	-	-	30	-	$\mu V/°C$
Bias Current	25	-	100	200	-	125	250	nA
	Full	-	-	400	-	-	500	nA
Offset Current	25	-	10	25	-	20	50	nA
	Full	-	-	50	-	-	100	nA
Input Resistance (Note 2)	25	50	100	-	40	100	-	M $\Omega$
Common Mode Range	Full	$\pm 10.0$	-	-	$\pm 10.0$	-	-	V
<b>TRANSFER CHARACTERISTICS</b>								
Large Signal Voltage Gain (Notes 3, 6)	25	10	15	-	7.5	15	-	kV/V
	Full	7.5	-	-	5	-	-	kV/V
Common Mode Rejection Ratio (Note 4)	Full	80	90	-	74	90	-	dB
Gain Bandwidth (Notes 2, 5)	25	10	20	-	10	20	-	MHz
Minimum Stable Gain	25	3	-	-	3	-	-	V/V
<b>OUTPUT CHARACTERISTICS</b>								
Output Voltage Swing (Note 3)	Full	$\pm 10.0$	$\pm 12.0$	-	$\pm 10.0$	$\pm 12.0$	-	V
Output Current (Note 6)	25	$\pm 10$	$\pm 20$	-	$\pm 10$	$\pm 20$	-	mA
Full Power Bandwidth (Notes 6, 11)	25	1.5	2.0	-	1.2	2.0	-	MHz
<b>TRANSIENT RESPONSE (<math>A_V = +3</math>)</b>								
Rise Time (Notes 3, 7, 8, 10)	25	-	25	50	-	25	50	ns
Overshoot (Notes 3, 7, 8, 10)	25	-	25	40	-	25	50	%
Slew Rate (Notes 3, 7, 10, 12)	25	$\pm 100$	$\pm 120$	-	$\pm 80$	$\pm 120$	-	V/ $\mu s$
Settling Time (Notes 3, 7, 10, 12)	25	-	0.20	-	-	0.20	-	$\mu s$
<b>POWER SUPPLY CHARACTERISTICS</b>								
Supply Current	25	-	4	6	-	4	6	mA

**Electrical Specifications**  $V_{SUPPLY} = \pm 15V$  (Continued)

PARAMETER	TEMP (°C)	HA-2520-2			HA-2525-5			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
Power Supply Rejection Ratio (Note 9)	Full	80	90	-	74	90	-	dB

NOTES:

2. This parameter value is based on design calculations.
3.  $R_L = 2k\Omega$ .
4.  $V_{CM} = \pm 10V$ .
5.  $A_V > 10$ .
6.  $V_O = \pm 10.0V$ .
7.  $C_L = 50pF$ .
8.  $V_O = \pm 200mV$ .
9.  $\Delta V = \pm 5.0V$ .
10. See Transient Response Test Circuits and Waveforms.
11. Full Power Bandwidth guaranteed based on slew rate measurement using:  $FPBW = \frac{Slew\ Rate}{2\pi V_{PEAK}}$ .
12.  $V_{OUT} = \pm 5V$ .

**Test Circuits and Waveforms**

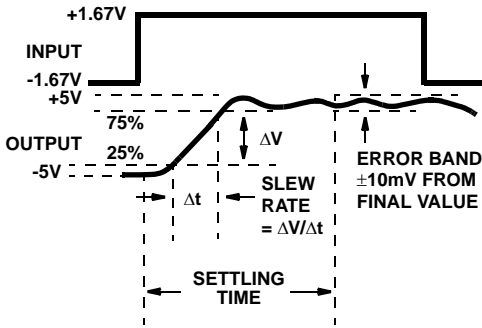
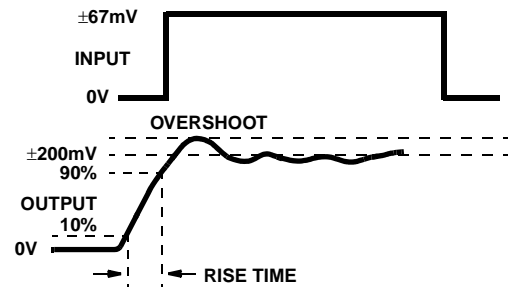


FIGURE 1. SLEW RATE AND SETTLE TIME



NOTE: Measured on both positive and negative transitions from 0V to +200mV and 0V to -200mV at the output.

FIGURE 2. TRANSIENT RESPONSE

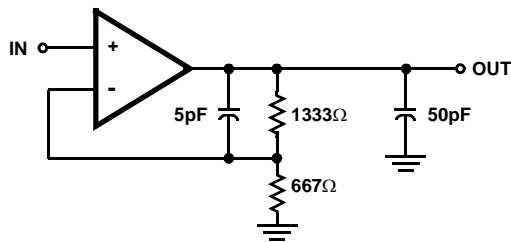
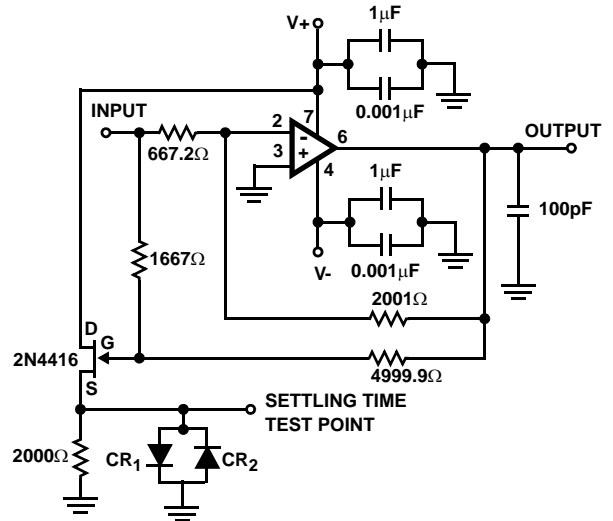


FIGURE 3. SLEW RATE AND TRANSIENT RESPONSE



NOTES:

13.  $A_V = -3$ .
14. Feedback and summing resistor ratios should be 0.1% matched.
15. Clipping diodes  $CR_1$  and  $CR_2$  are optional. HP5082-2810 recommended.

FIGURE 4. SETTLE TIME TEST CIRCUIT

**Die Characteristics**

**METALLIZATION:**

Type: Al, 1% Cu  
 Thickness:  $16k\text{\AA} \pm 2k\text{\AA}$

Silox Thickness:  $12k\text{\AA} \pm 2k\text{\AA}$   
 Nitride Thickness:  $3.5k\text{\AA} \pm 1.5k\text{\AA}$

**SUBSTRATE POTENTIAL:**

Unbiased

**TRANSISTOR COUNT:**

40

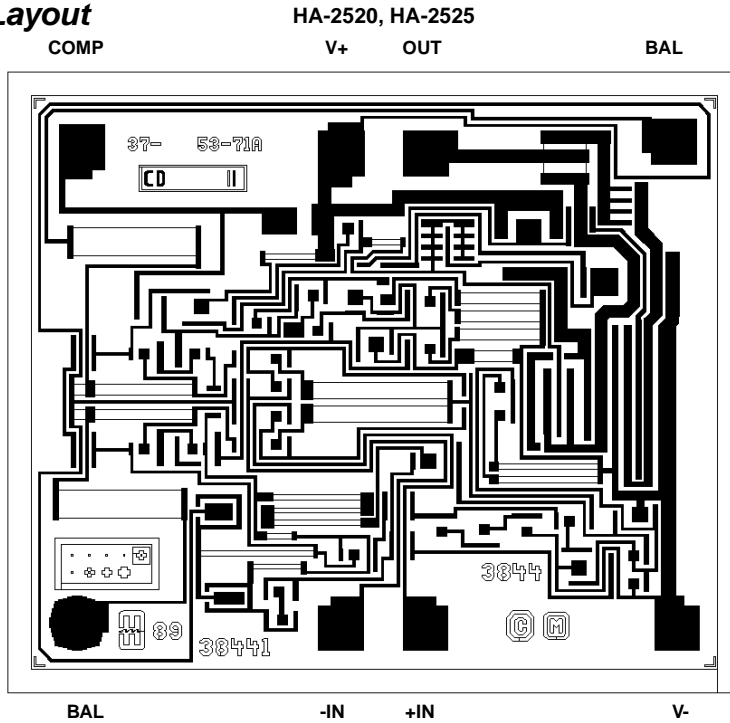
**PASSIVATION:**

Type: Nitride ( $\text{Si}_3\text{N}_4$ ) over Silox ( $\text{SiO}_2$ , 5% Phos.)

**PROCESS:**

Bipolar Dielectric Isolation

**Metallization Mask Layout**



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